

## Description

The FDN5630 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

#### **General Features**

$$\begin{split} V_{\text{DS}} &= 60 V \ \text{I}_{\text{D}} = 3 \text{A} \\ \text{R}_{\text{DS(ON)}} &< 89 \text{m} \Omega \ @ \ \text{V}_{\text{GS}} = 10 V \end{split}$$

### Application

Battery protection Load switch Uninterruptible power supply

#### Package Marking and Ordering Information

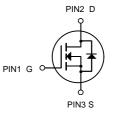
Product ID	Pack	Marking	Qty(PCS)
FDN5630	SOT-23	S10	3000PCS

### Absolute Maximum Ratings (T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

Symbol	Symbol Parameter		Unit	
VDS	Drain-Source Voltage	60	V	
Vgs	Gate-Source Voltage	±20	V	
I <sub>D</sub>	Drain Current-Continuous	3	А	
Ы	Drain Current-Pulsed (Note 1)	10	А	
PD	Maximum Power Dissipation	1.7	W	
TJ,Tstg	Operating Junction and Storage Temperature Range	-55 To 150	°C	
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)	73.5	°C <b>/W</b>	







N-Channel MOSFET



## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20V, $V_{DS}$ =0V	-	-	±100	nA
On Characteristics (Note 3)				•		
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250µA	0.8	1.3	2.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =3A	-	80	89	mΩ
Drain-Source On-State Resistance		V <sub>GS</sub> =4.5V, I <sub>D</sub> =1.5A	-	89	115	mΩ
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =15V,I <sub>D</sub> =2A		3	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>		-	510	-	PF
Output Capacitance	Coss	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V, F=1.0MHz	-	34	-	PF
Reverse Transfer Capacitance	Crss		-	26	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =30V,I <sub>D</sub> =1.5A	-	6	-	nS
Turn-on Rise Time	tr		-	15	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10V, $R_{GEN}$ =1 $\Omega$	-	15	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	10	-	nS
Total Gate Charge	Qg	)/ _20)// _20	-	7.5	-	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =30V,I <sub>D</sub> =3A, V <sub>GS</sub> =4.5V	-	1.4	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	v <sub>GS</sub> =4.5V	-	3	-	nC
Drain-Source Diode Characteristics	·		·	•		
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =3A	-	-	1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	3	Α

#### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

**2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.

**3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

4. Guaranteed by design, not subject to production



# **Typical Electrical and Thermal Characteristics**

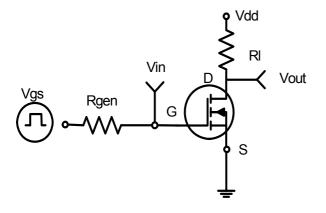


Figure 1:Switching Test Circuit

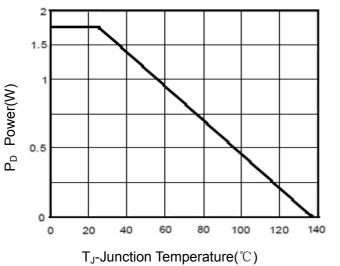
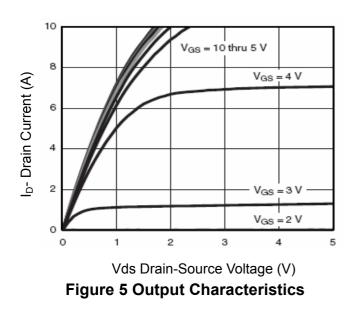
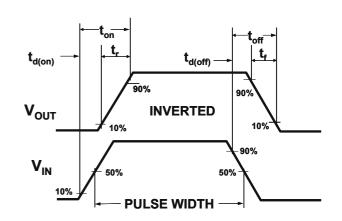
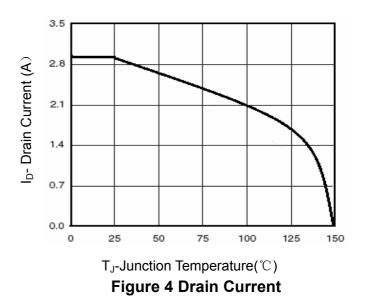


Figure 3 Power Dissipation





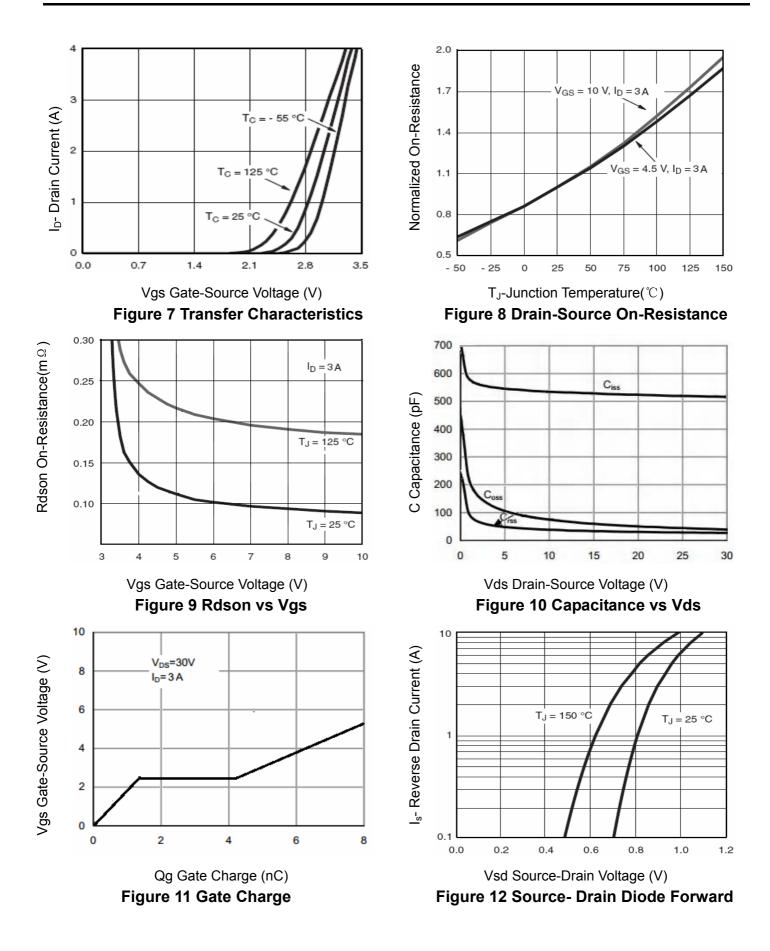




(c) 0.300.240.120.1









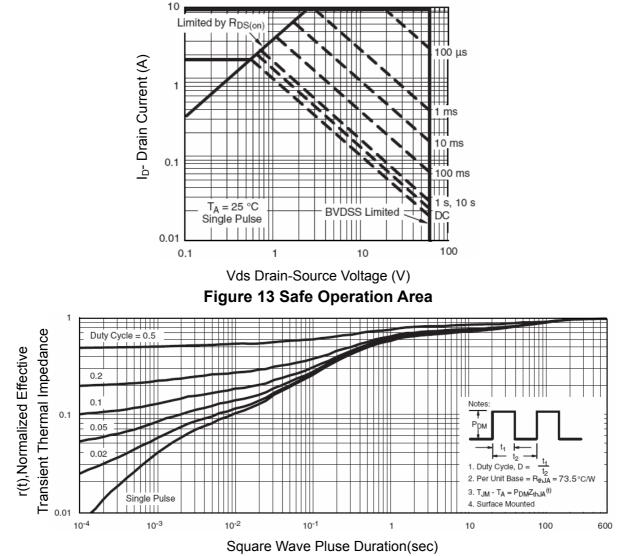
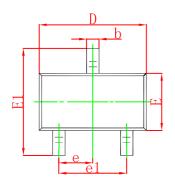
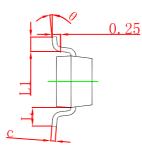


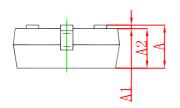
Figure 14 Normalized Maximum Transient Thermal Impedance



# **SOT-23 Package Outline Dimensions**

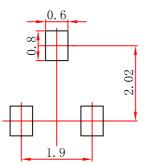






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
А	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

## SOT-23 Suggested Pad Layout



Note: 1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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